

Notice of References Cited	Application/Control No. 09/824,965		Applicant(s)/Patent Under Reexamination KAWASE ET AL.	
	Examiner Robert M. Kunemund		Art Unit 1722	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-5,131,975	07-1992	Bourret-Courchesne, Edith D.	117/82
*	C	US-5,515,810	05-1996	Yamashita, Youji	117/17
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*	U	Journal of Japanese Association of Crystal Growth, Y. Okabe et al, Undoped Semi-Insulating GaAs Single Crystals Grown by the VGF Method vol 18, 1991 pages 88-95
*	V	Kawase, T. " Low dislocation density and low residual strain semi-insulating GaAs grown by vertical boat method", April 1996
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.